



October 2006

UniFET™

FDAF75N28

280V N-Channel MOSFET

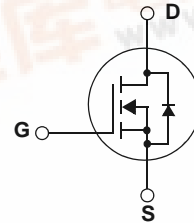
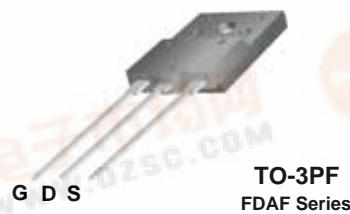
Features

- 46A, 280V, $R_{DS(on)} = 0.041\Omega @ V_{GS} = 10 V$
- Low gate charge (typical 111 nC)
- Low C_{rss} (typical 90 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor correction.



Absolute Maximum Ratings

Symbol	Parameter	FDAF75N28	Unit
V_{DSS}	Drain-Source Voltage	280	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ C$)	46
		- Continuous ($T_C = 100^\circ C$)	28
I_{DM}	Drain Current - Pulsed (Note 1)	184	A
V_{GSS}	Gate-Source voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	3080	mJ
I_{AR}	Avalanche Current (Note 1)	46	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	21.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ C$)	- Derate above $25^\circ C$	1.72
			215
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Min.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.58	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ C/W$

FDAF75N28 280V N-Channel MOSFET



Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDAF75N28	FDAF75N28	TO-3PF	--	--	30

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	280	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	--	0.28	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 280V, V _{GS} = 0V V _{DS} = 224V, T _C = 125°C	--	--	1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 23A	--	0.035	0.041	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 23A (Note 4)	--	75	--	S
Dynamic Characteristics						
C _{iSS}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	--	5040	6700	pF
C _{oSS}	Output Capacitance		--	915	1215	pF
C _{rSS}	Reverse Transfer Capacitance		--	90	135	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 140V, I _D = 75A R _G = 25Ω (Note 4, 5)	--	105	146	ns
t _r	Turn-On Rise Time		--	580	538	ns
t _{d(off)}	Turn-Off Delay Time		--	190	418	ns
t _f	Turn-Off Fall Time		--	310	262	ns
Q _g	Total Gate Charge	V _{DS} = 224V, I _D = 75A V _{GS} = 10V (Note 4, 5)	--	111	144	nC
Q _{gs}	Gate-Source Charge		--	31	--	nC
Q _{gd}	Gate-Drain Charge		--	49	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	75	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	300	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 46A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 75A	--	320	--	ns
Q _{rr}	Reverse Recovery Charge	di _F /dt = 100A/μs (Note 4)	--	3.5	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 2.4mH, I_{AS} = 46A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 46A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

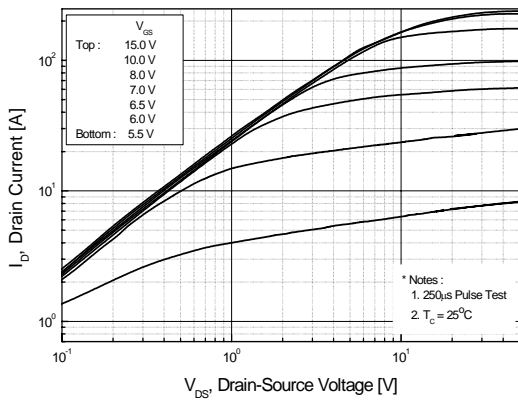


Figure 2. Transfer Characteristics

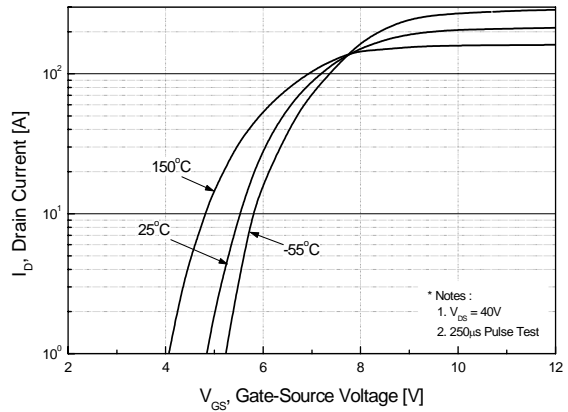


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

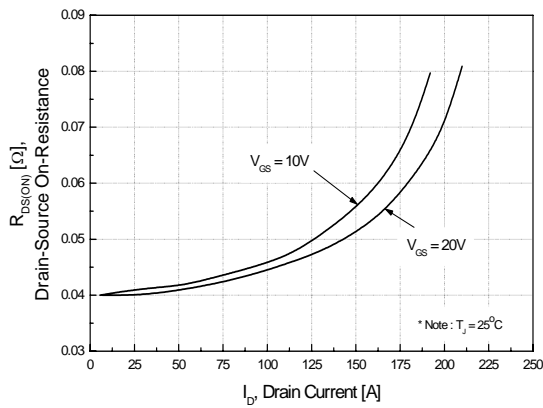


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

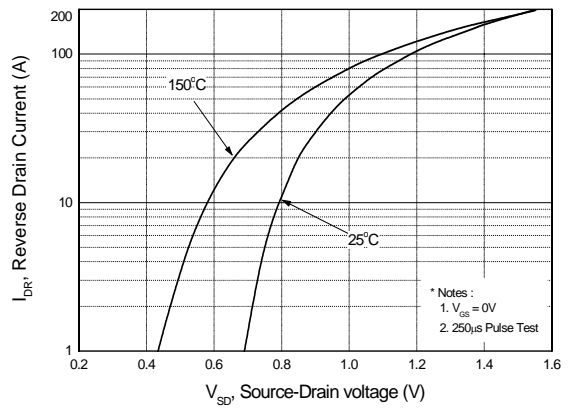


Figure 5. Capacitance Characteristics

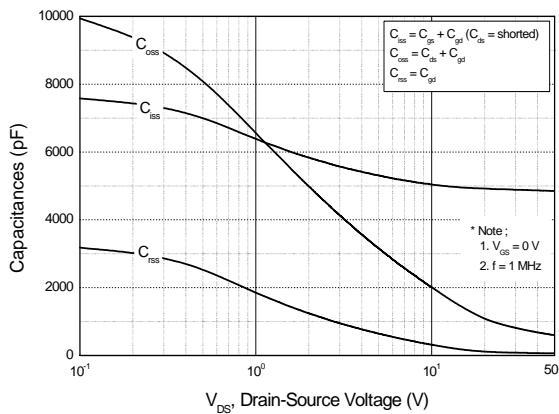
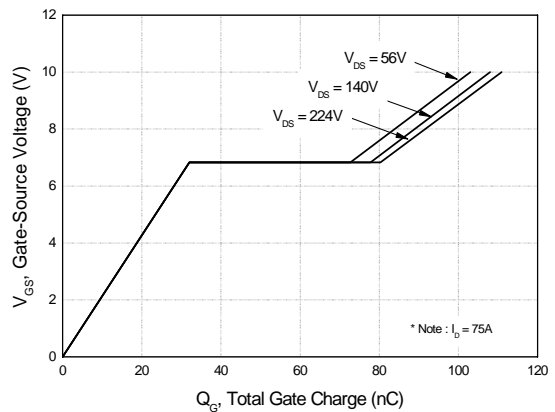


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

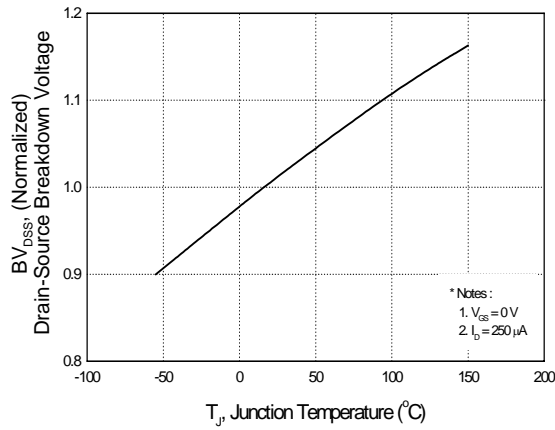


Figure 8. On-Resistance Variation vs. Temperature

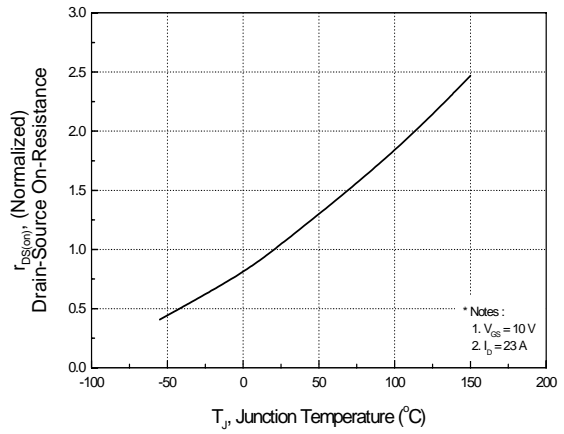


Figure 9. Safe Operating Area

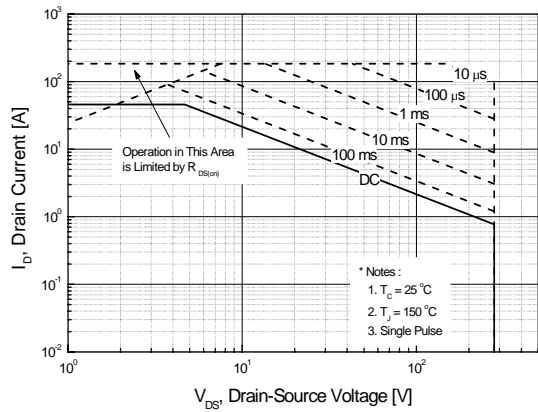


Figure 10. Maximum Drain Current vs. Case Temperature

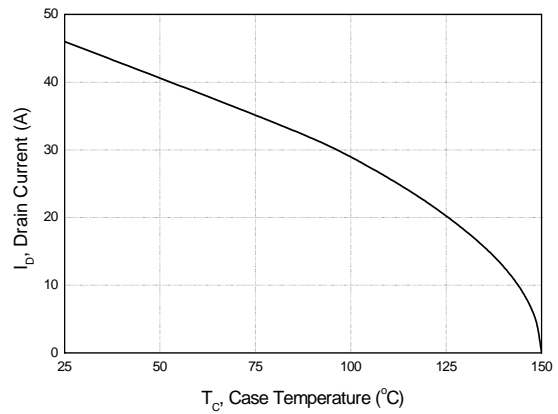
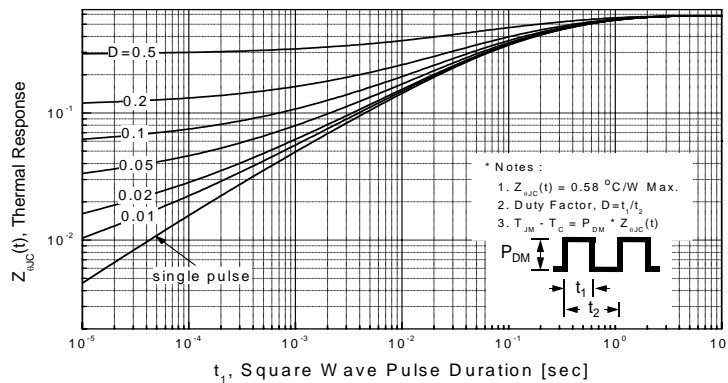
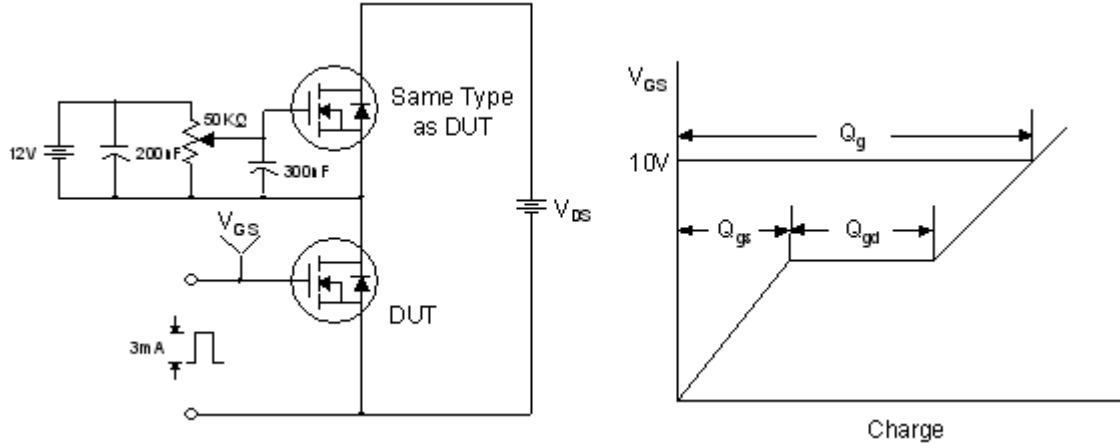


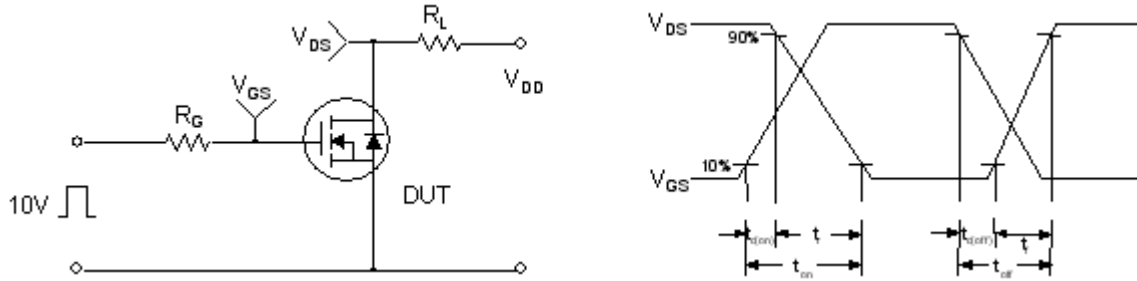
Figure 11. Transient Thermal Response Curve



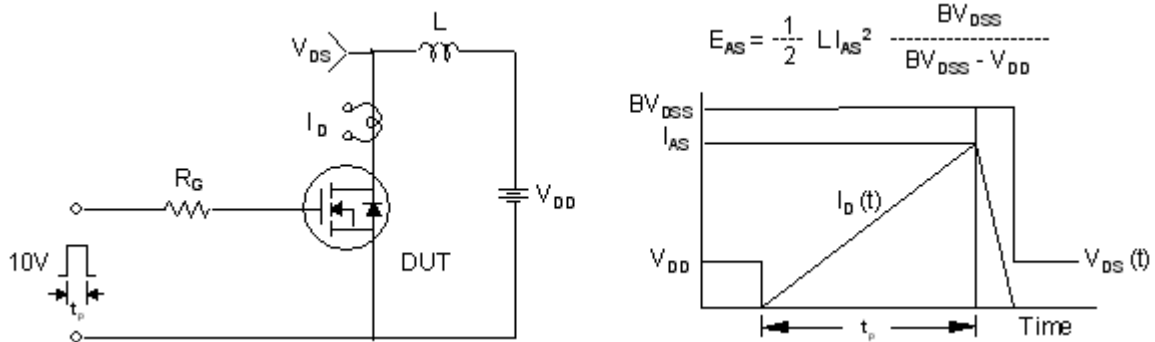
Gate Charge Test Circuit & Waveform



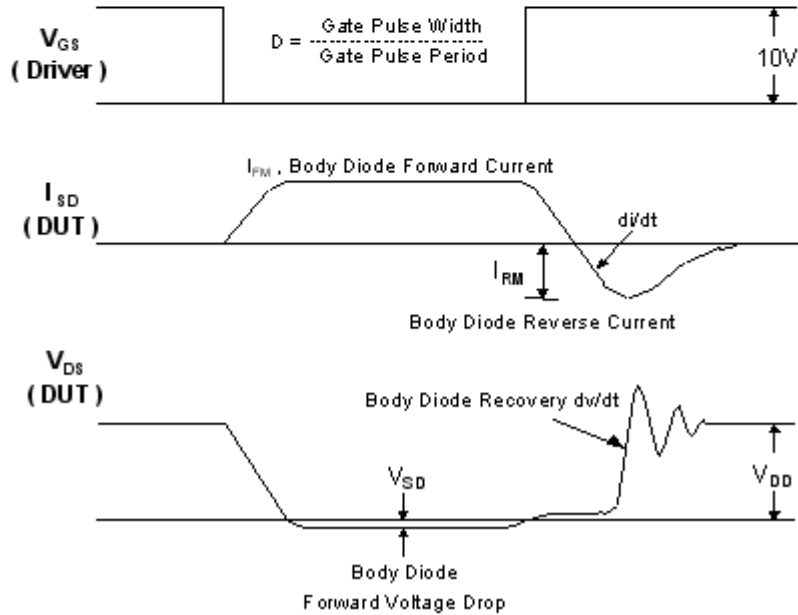
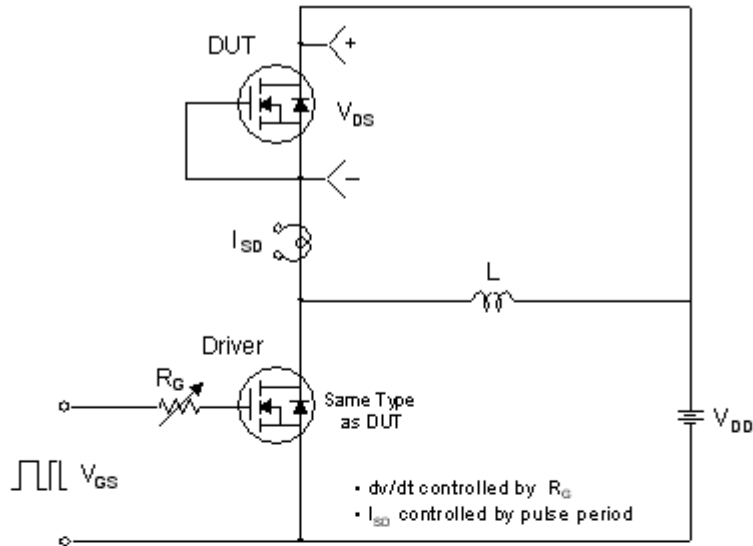
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

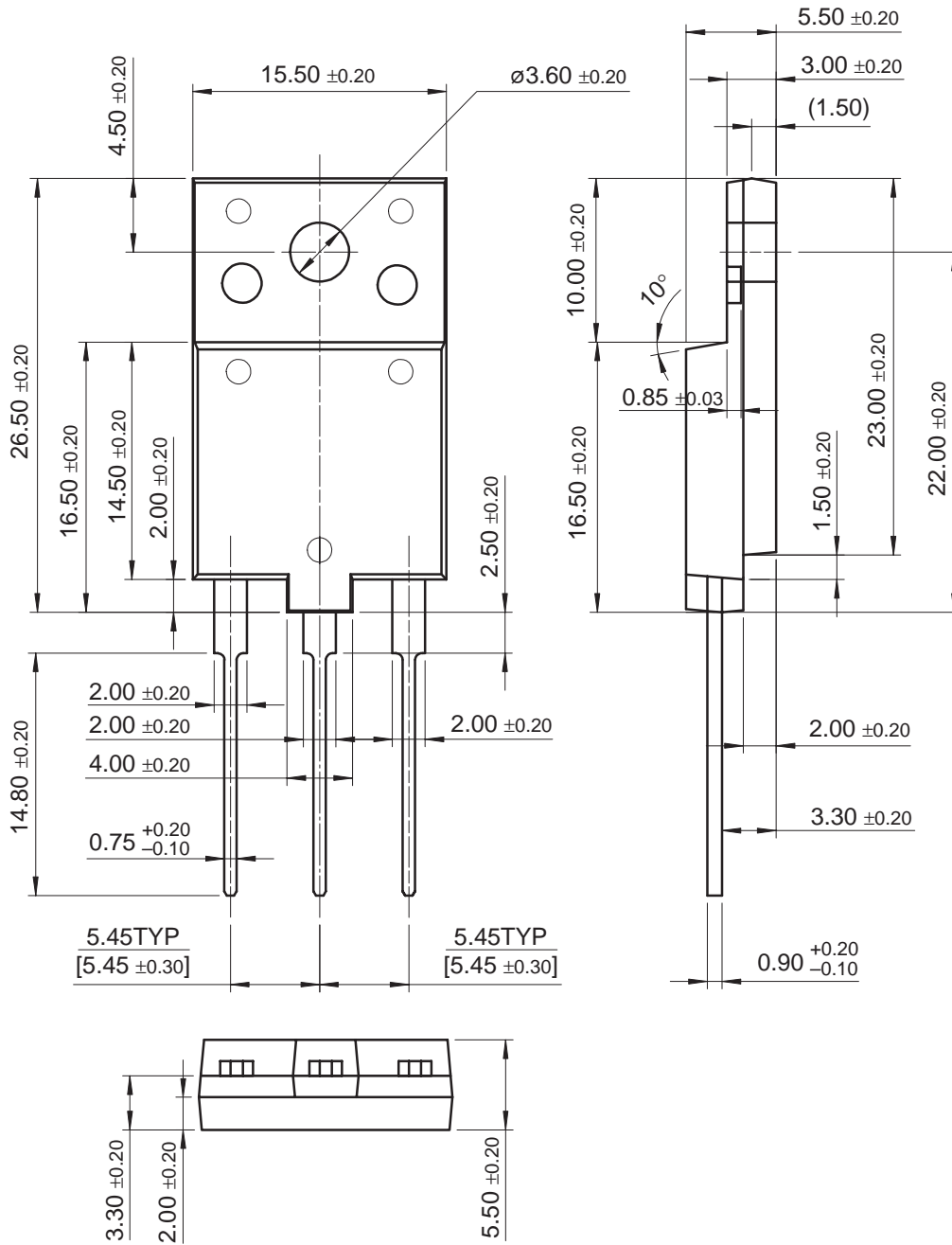


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-3PF



Dimensions in Millimeters

